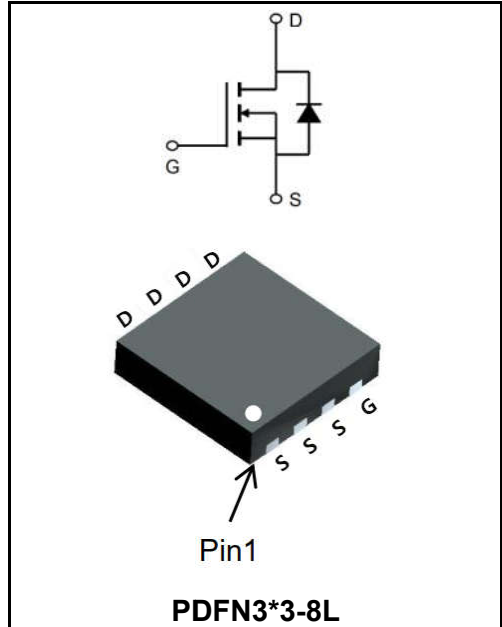


30V N-CHANNEL ENHANCEMENT MODE MOSFET

MAIN CHARACTERISTICS

I_D	60A
V_{DSS}	30V
R_{DS(on)-typ(@V_{GS}=10V)}	< 8.5mΩ (Type:6.0 mΩ)



Application

- ◆VBUS
- ◆Wireless impact
- ◆Mobile phone fast charging

Product Specification Classification

Part Number	Package	Marking	Pack
YFW60N03DF	PDFN3*3-8L	YFW 60N03DF XXXXX	5000PCS/Tape

Maximum Ratings at T_c=25°C unless otherwise specified

Characteristics	Symbols	Value	Units
Drain-Source Voltage	V_{DS}	30	V
Gate - Source Voltage	V_{GS}	±20	V
Continuous Drain Current, V _{GS} @ 10V ¹ @T _c =25°C	I_D	60	A
Continuous Drain Current, V _{GS} @ 10V ¹ @T _c =100°C	I_D	29	A
Pulsed Drain Current ²	I_{DM}	92	A
Single Pulse Avalanche Energy ³	E_{AS}	57.8	mJ
Avalanche Current	I_{AS}	34	A
Total Power Dissipation ⁴ @T _c =25°C	P_D	29	W
Storage Temperature Range	T_{STG}	-55 to +150	°C
Operating Junction Temperature Range	T_J	-55 to +150	°C
Thermal Resistance, Junction-to-Ambient ¹	R_{θJA}	62.5	°C/W
Thermal Resistance Junction-Case ¹	R_{θJC}	4.32	°C/W

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	BV_{DSS}	30	33	-	V
Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=12A$	$R_{DS(ON)}$	-	6.0	8.5	mΩ
	$V_{GS}=4.5V, I_D=10A$		-	8.0	13	
Gate -Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	$V_{GS(th)}$	1.0	1.6	2.5	V
$V_{GS(th)}$ Temperature Coefficient		$V_{GS(th)}$	-	-5.8	-	mV/°C
Drain -Source Leakage Current	$V_{DS}=24V, V_{GS}=0V, T_J=25^\circ C$	I_{DSS}	-	-	1	μA
	$V_{DS}=24V, V_{GS}=0V, T_J=55^\circ C$		-	-	5	
Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	I_{GSS}	-	-	±100	nA
Forward Transconductance	$V_{DS}=5V, I_D=15A$	g_{FS}	-	9.8	-	S
Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1MHz$	R_g	-	1.7	-	Ω
Total Gate Charge(4.5V)	$V_{DS}=20V$ $V_{GS}=4.5V$ $I_D=12A$	Q_g	-	12.8	-	nC
Gate-Source Charge		Q_{gs}	-	3.3	-	
Gate-Drain Charge		Q_{gd}	-	6.5	-	
Turn-on delay time	$V_{DD}=12V$ $V_{GS}=10V$ $R_G=3.3\Omega$ $I_D=5A$	$t_{d(on)}$	-	4.5	-	ns
Rise Time		T_r	-	10.8	-	
Turn-Off Delay Time		$t_{d(OFF)}$	-	25.5	-	
Fall Time		t_f	-	9.6	-	
Input Capacitance	$V_{DS}=15V$ $V_{GS}=0V$ $f=1.0MHz$	C_{iss}	-	1317	-	pF
Output Capacitance		C_{oss}	-	163	-	
Reverse Transfer Capacitance		C_{rss}	-	131	-	
Continuous Source Current ^{1,5}	$V_G=V_D=0V, \text{ Force Current}$	I_S	-	-	46	A
Pulsed Source Current ^{2,6}		I_{SM}	-	-	92	A
Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^\circ C$	V_{SD}	-	-	1	V

Note :

- 1、 The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.
- 2、 The data tested by pulsed , pulse width $\cong 300\mu s$, duty cycle $\cong 2\%$
- 3、 The EAS data shows Max. rating . The test condition is $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=34A$
- 4、 The power dissipation is limited by 150°C junction temperature
- 5、 The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Ratings and Characteristic Curves

Typical Characteristics

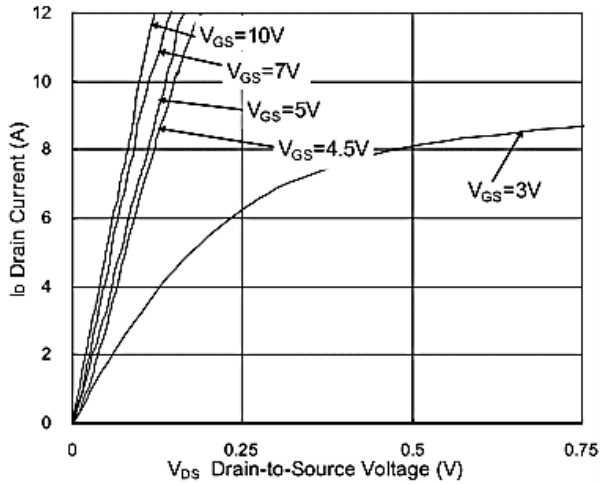


Fig.1 Typical Output Characteristics

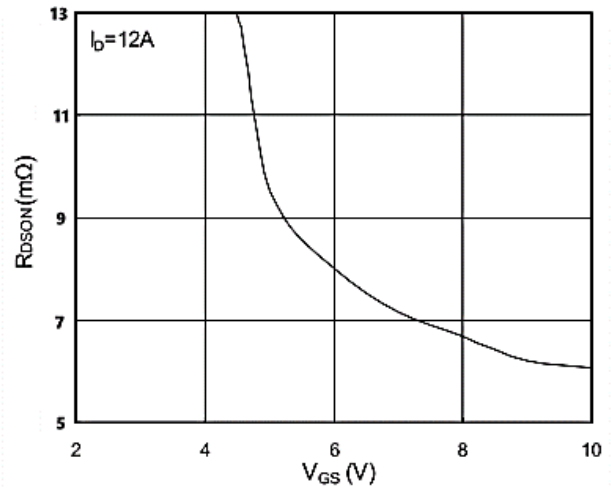


Fig.2 On-Resistance vs. G-S Voltage

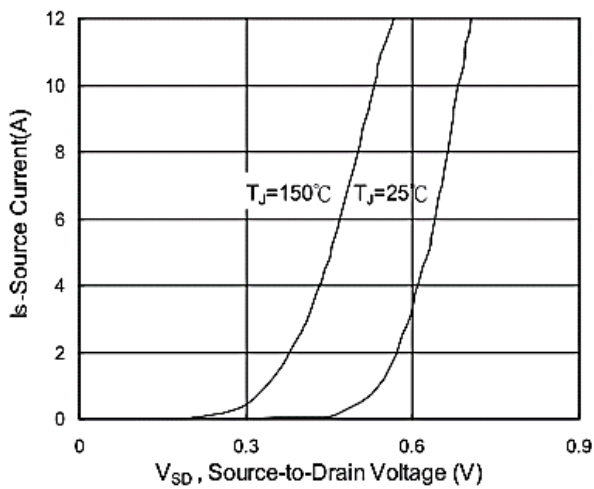


Fig.3 Forward Characteristics of Reverse

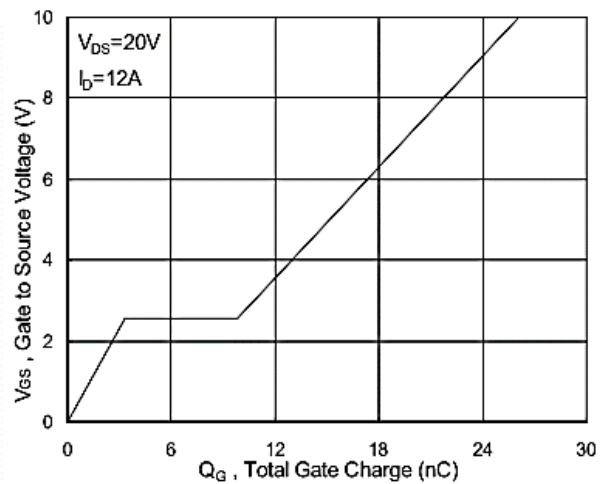


Fig.4 Gate-Charge Characteristics

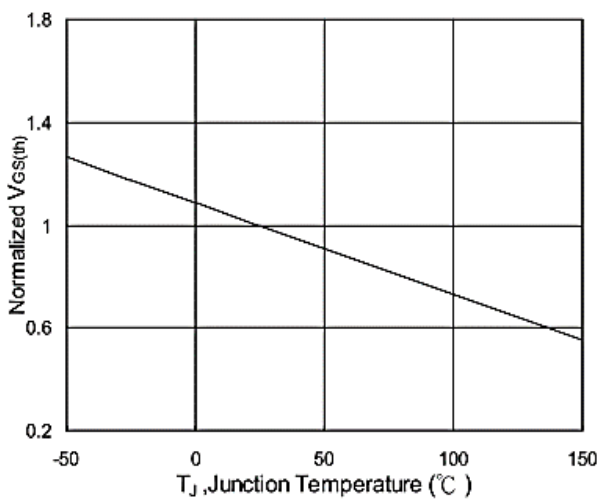


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

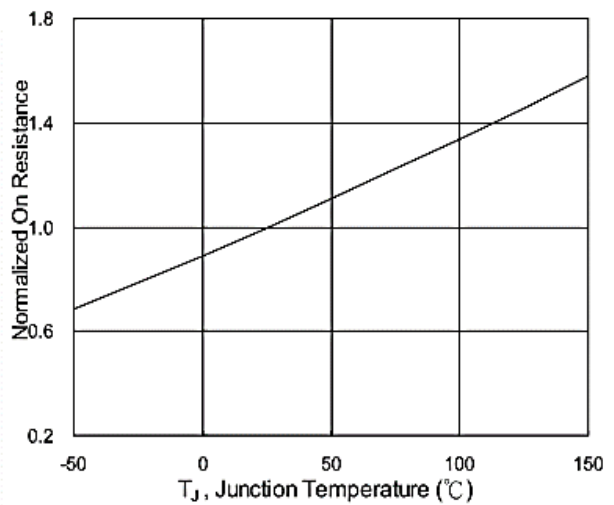


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

Ratings and Characteristic Curves

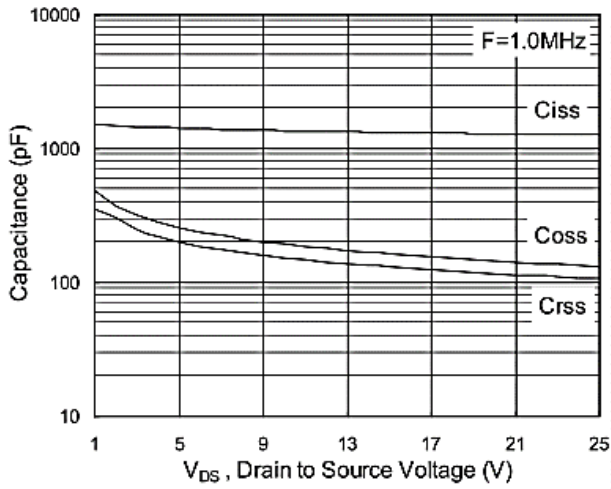


Fig.7 Capacitance

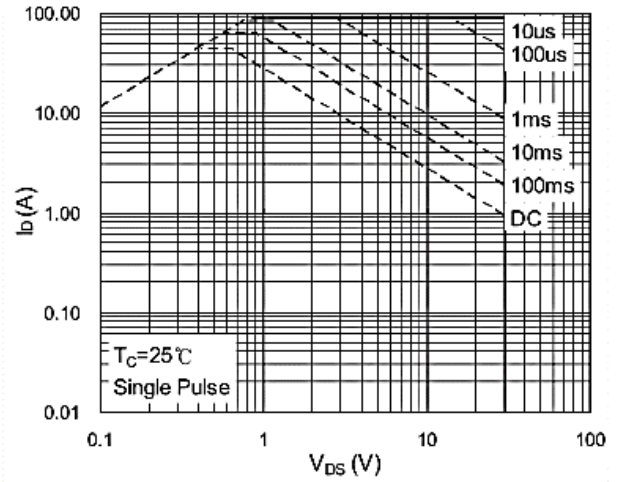


Fig.8 Safe Operating Area

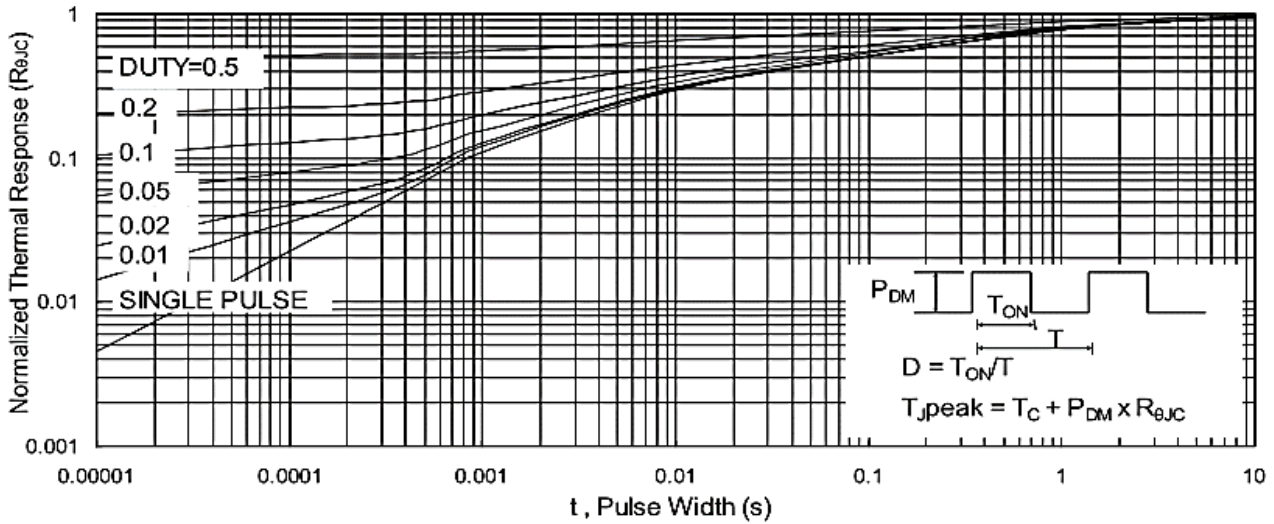


Fig.9 Normalized Maximum Transient Thermal Impedance

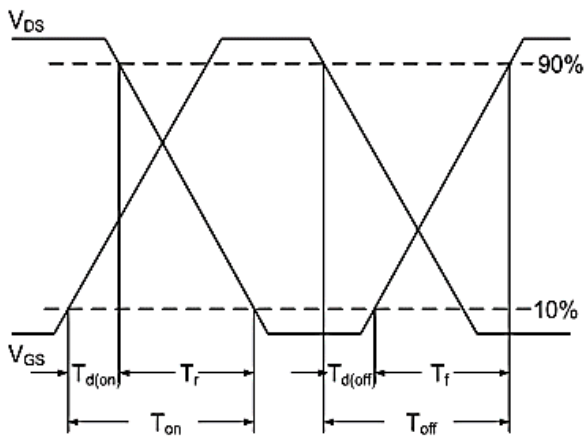


Fig.10 Switching Time Waveform

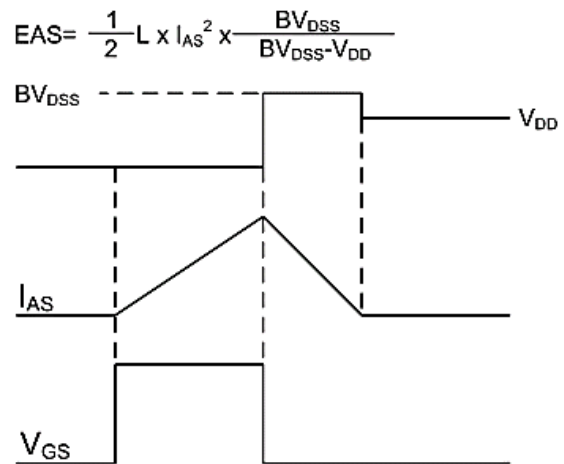
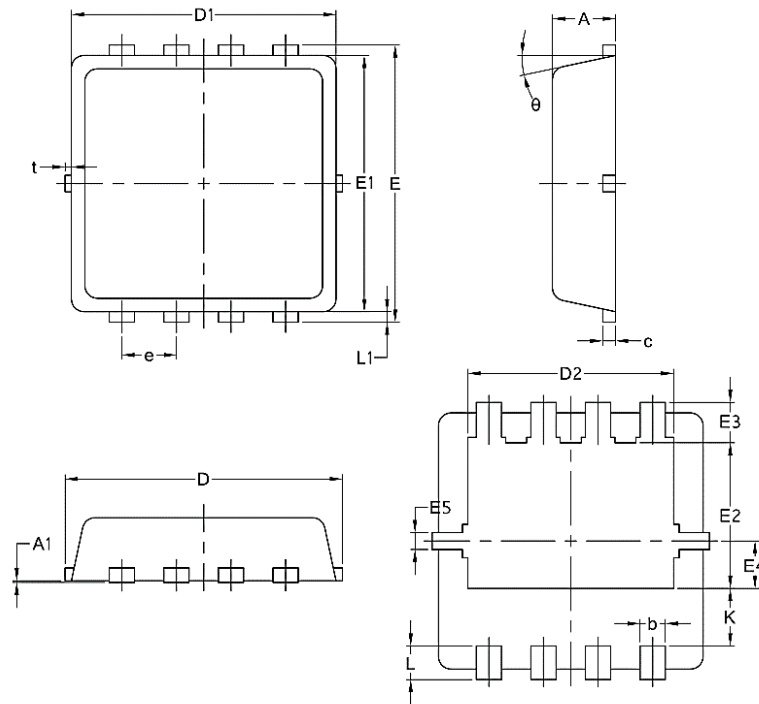


Fig.11 Unclamped Inductive Switching Waveform

PDFN3*3-8L



Symbol	Common		
	mm		
	Mim	Nom	Max
A	0.70	0.75	0.85
A1	/	/	0.05
b	0.20	0.30	0.40
c	0.10	0.152	0.25
D	3.15	3.30	3.45
D1	3.00	3.15	3.25
D2	2.29	2.45	2.65
E	3.15	3.30	3.45
E1	2.90	3.05	3.20
E2	1.54	1.74	1.94
E3	0.28	0.48	0.65
E4	0.37	0.57	0.77
E5	0.10	0.20	0.30
e	0.60	0.65	0.70
K	0.59	0.69	0.89
L	0.30	0.40	0.50
L1	0.06	0.125	0.20
t	0	0.075	0.13
Φ	10	12	14